



JMT250KT18T3

- Half-bridge SCR configuration integrated in a single package
- With high thermal conductivity DBC as the Insulation
- Welding by vacuum welding technology, which provide high reliability

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{T(AV)}$ (@ $T_C = 85^\circ\text{C}$)	250	A
I_{TSM} (@ t_P)		

Applications

- Temperature control
- Light control system
- DC motor

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak off-state voltage	$T_{vj} = 25^\circ\text{C}$	V_{DRM}	1800	V
Repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RRM}	1800	V
Non-repetitive peak off-state voltage	$T_{vj} = 25^\circ\text{C}$	V_{DSM}	1900	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ\text{C}$	V_{RSM}	1900	V
Average forward current	$T_C = 85^\circ\text{C}$	$I_{T(AV)}$	250	A
Forward surge current	$t_P=10\text{ms } V_R=0.6V_{RRM}$	I_{TSM}	8300	A
I^2t value for fusing		I^2t	344450	A^2s
Critical rate of rise of on-state current	$I_G=2 \times I_{GT}$	di/dt	150	$\text{A}/\mu\text{s}$
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +125	

Storage temperature range: -40 to +125°C (per)-3.4 (a)1310.48 05eM2a




Electrical Characteristics (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	

Peak forward voltage $I_T =$



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